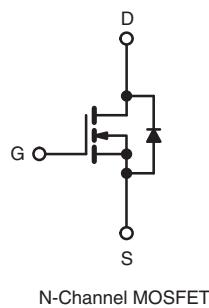
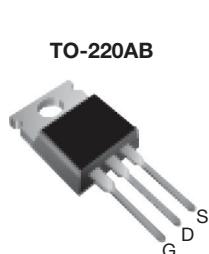


## Power MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	60	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10$ V	0.028
$Q_g$ (Max.) (nC)	67	
$Q_{gs}$ (nC)	18	
$Q_{gd}$ (nC)	25	
Configuration	Single	



### FEATURES

- Dynamic  $dV/dt$  Rating
- 175 °C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC


**RoHS\***  
COMPLIANT

### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

### ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRFZ44PbF SiHFZ44-E3
SnPb	IRFZ44 SiHFZ44

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>a</sup>	$I_D$	50	A
Continuous Drain Current		36	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	200	
Linear Derating Factor		1.0	W/°C
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	100	mJ
Maximum Power Dissipation	$P_D$	150	W
Peak Diode Recovery $dV/dt^c$	$dV/dt$	4.5	V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature) <sup>d</sup>	for 10 s	300	
Mounting Torque	6-32 or M3 screw	10 1.1	lbf · in N · m

#### Notes

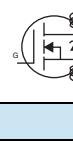
- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25$  V, starting  $T_J = 25$  °C,  $L = 44$   $\mu$ H,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 51$  A (see fig. 12).
- $I_{SD} \leq 51$  A,  $dI/dt \leq 250$  A/ $\mu$ s,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 175$  °C.
- 1.6 mm from case.
- Current limited by the package, (die current = 51 A).

\* Pb containing terminations are not RoHS compliant, exemptions may apply

**THERMAL RESISTANCE RATINGS**

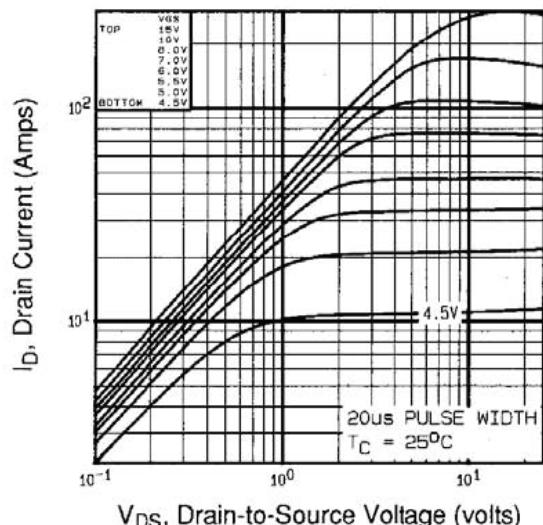
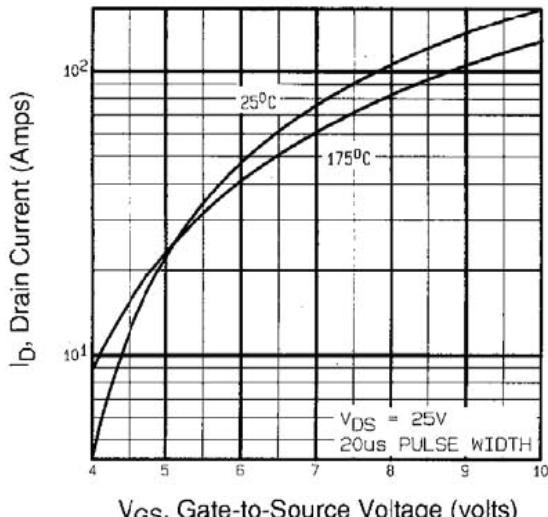
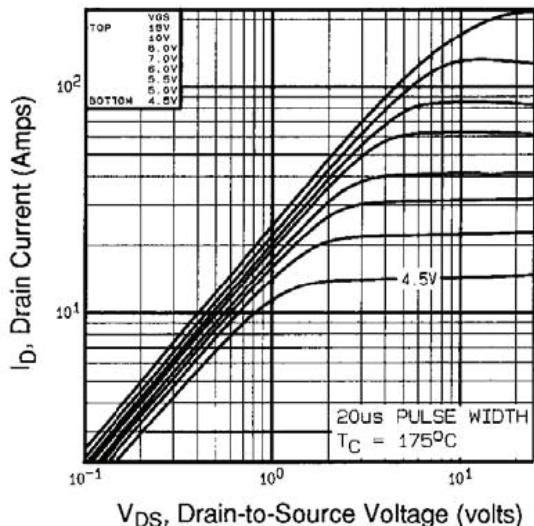
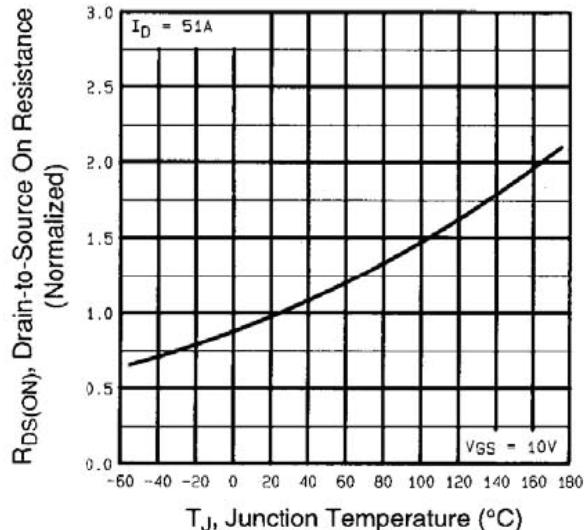
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	$^{\circ}\text{C}/\text{W}$
Case-to-Sink, Flat, Greased Surface	$R_{thCS}$	0.50	-	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	1.0	

**SPECIFICATIONS** ( $T_J = 25^{\circ}\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	60	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25^{\circ}\text{C}$ , $I_D = 1 \text{ mA}$	-	0.060	-	$^{\circ}\text{C}/\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60 \text{ V}$ , $V_{GS} = 0 \text{ V}$	-	-	25	$\mu\text{A}$
		$V_{DS} = 48 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $T_J = 125^{\circ}\text{C}$	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$	$I_D = 31 \text{ A}^b$	-	-	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 25 \text{ V}$ , $I_D = 31 \text{ A}$		15	-	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0 \text{ V}$ , $V_{DS} = 25 \text{ V}$ , $f = 1.0 \text{ MHz}$ , see fig. 5	-	1900	-	pF
Output Capacitance	$C_{oss}$		-	920	-	
Reverse Transfer Capacitance	$C_{rss}$		-	170	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10 \text{ V}$	$I_D = 51 \text{ A}$ , $V_{DS} = 48 \text{ V}$ , see fig. 6 and 13 <sup>b</sup>	-	67	nC
Gate-Source Charge	$Q_{gs}$			-	18	
Gate-Drain Charge	$Q_{gd}$			-	25	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30 \text{ V}$ , $I_D = 51 \text{ A}$ , $R_g = 9.1 \Omega$ , $R_D = 0.55 \Omega$ , see fig. 10 <sup>b</sup>	-	14	-	ns
Rise Time	$t_r$		-	110	-	
Turn-Off Delay Time	$t_{d(off)}$		-	45	-	
Fall Time	$t_f$		-	92	-	
Internal Drain Inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	nH
Internal Source Inductance	$L_S$			-	7.5	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode		-	-	50
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$			-	-	200
Body Diode Voltage	$V_{SD}$	$T_J = 25^{\circ}\text{C}$ , $I_S = 51 \text{ A}$ , $V_{GS} = 0 \text{ V}^b$	-	-	2.5	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}\text{C}$ , $I_F = 51 \text{ A}$ , $dl/dt = 100 \text{ A}/\mu\text{s}$	-	120	180	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	0.53	0.80	nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )				

**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
b. Pulse width  $\leq 300 \mu\text{s}$ ; duty cycle  $\leq 2 \%$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1** Typical Output Characteristics,  $T_C = 25^\circ\text{C}$ 

**Fig. 3** - Typical Transfer Characteristics

**Fig. 2** - Typical Output Characteristics,  $T_C = 175^\circ\text{C}$ 

**Fig. 4** - Normalized On-Resistance vs. Temperature

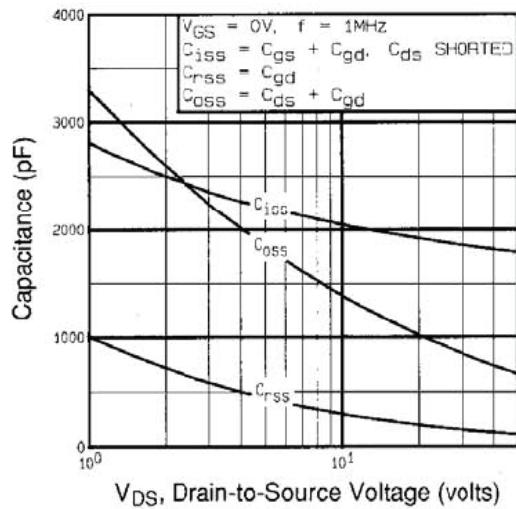


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

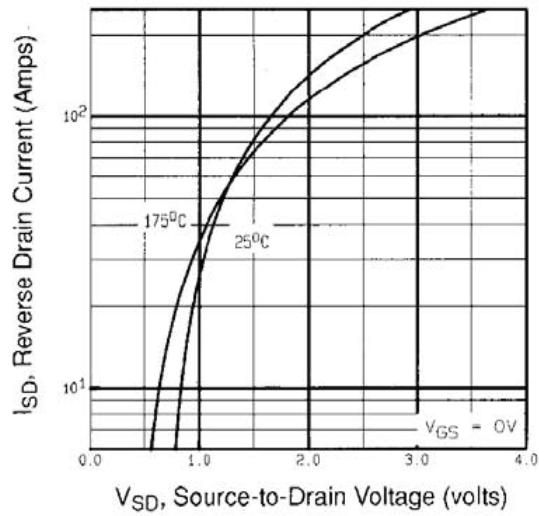


Fig. 7 - Typical Source-Drain Diode Forward Voltage

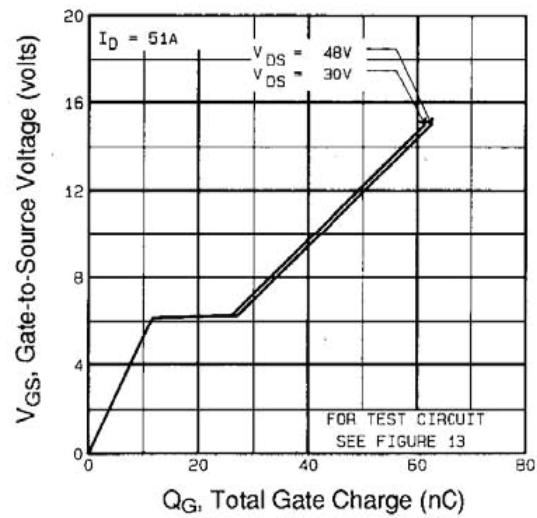
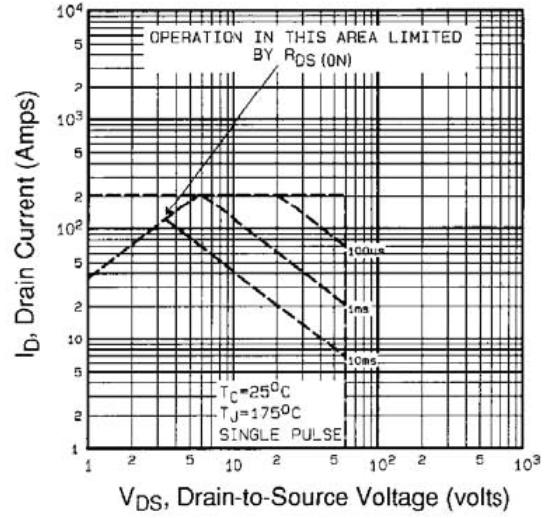


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



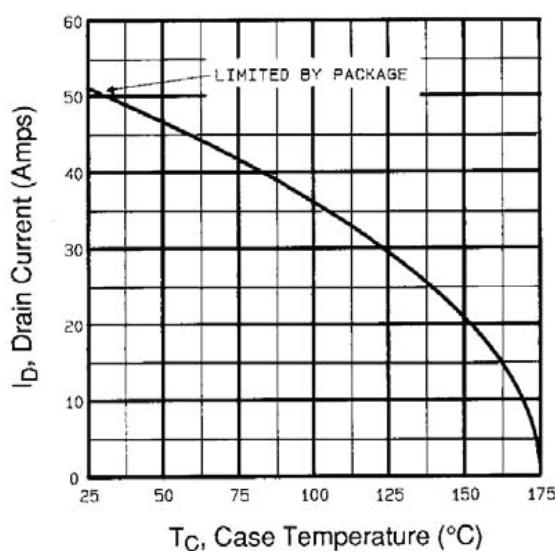


Fig. 9 - Maximum Drain Current vs. Case Temperature

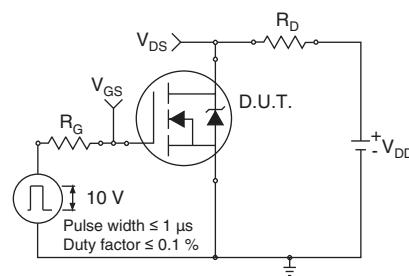


Fig. 10a - Switching Time Test Circuit

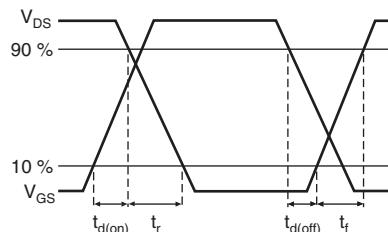


Fig. 10b - Switching Time Waveforms

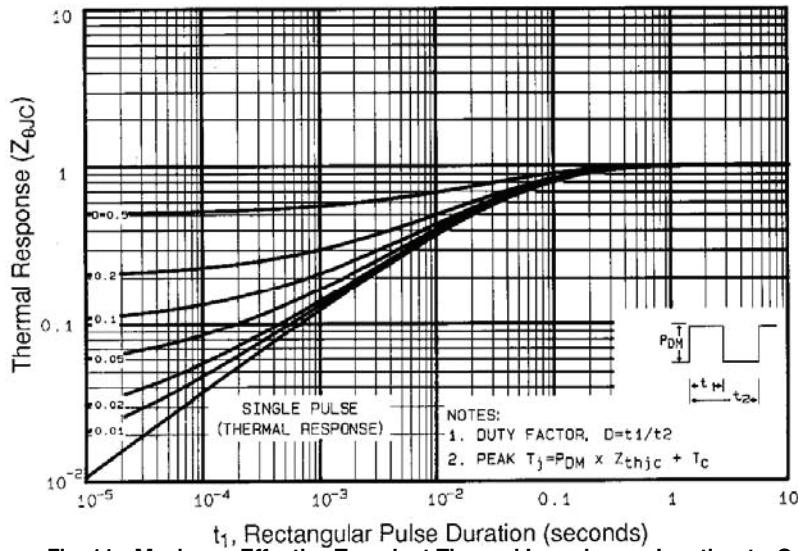


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

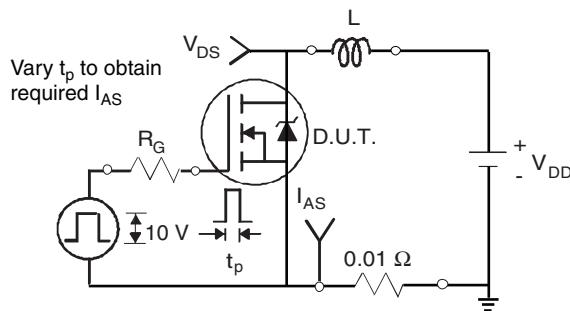


Fig. 12a - Unclamped Inductive Test Circuit

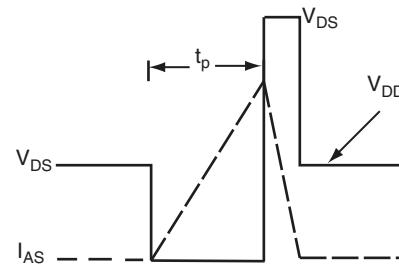


Fig. 12b - Unclamped Inductive Waveforms

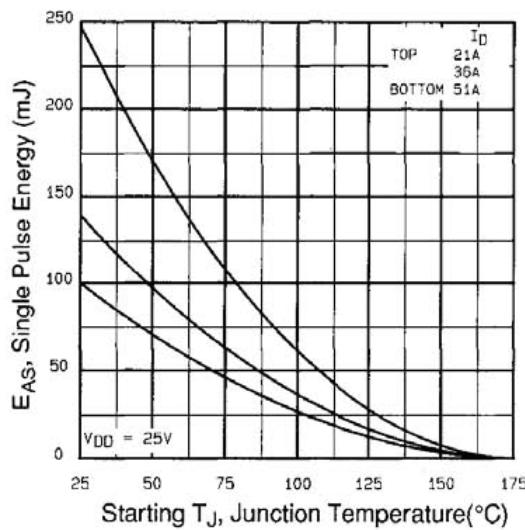


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

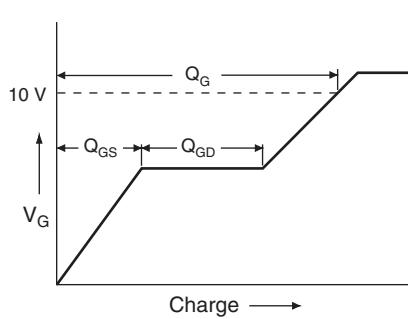


Fig. 13a - Basic Gate Charge Waveform

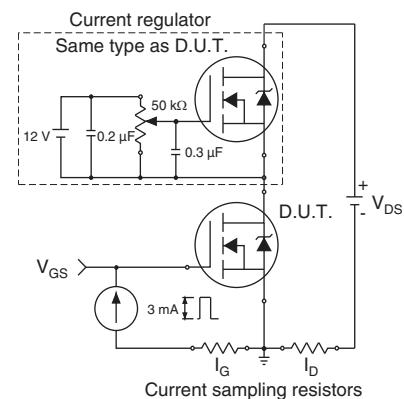
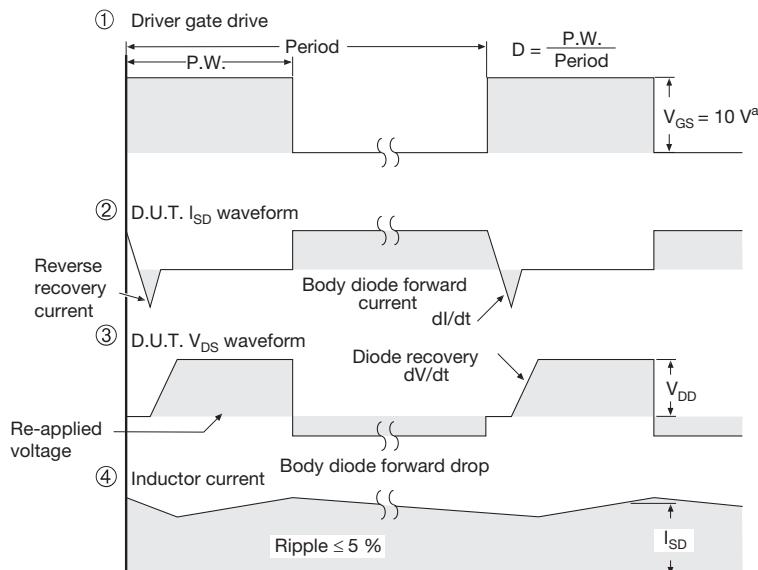
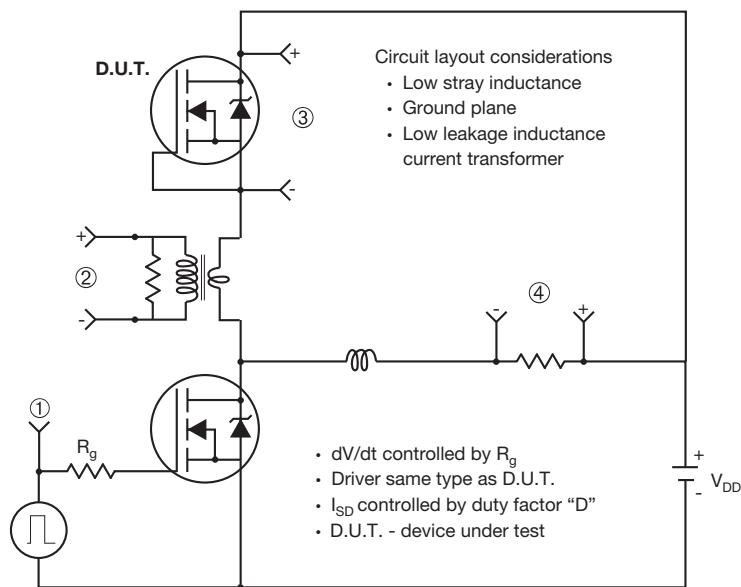


Fig. 13b - Gate Charge Test

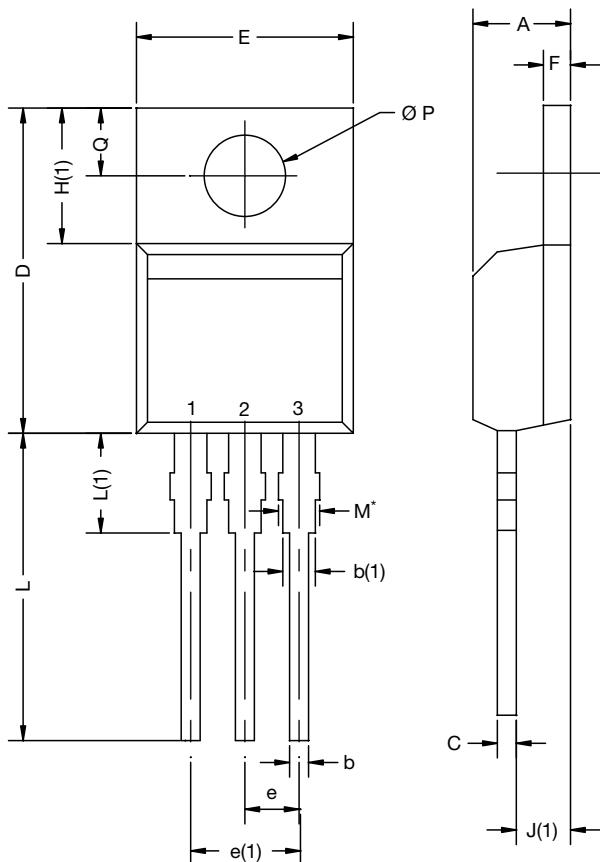
**Peak Diode Recovery dV/dt Test Circuit**

**Note**

a.  $V_{GS} = 5 \text{ V}$  for logic level devices

**Fig. 14 - For N-Channel**

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### TO-220-1



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15  
DWG: 6031

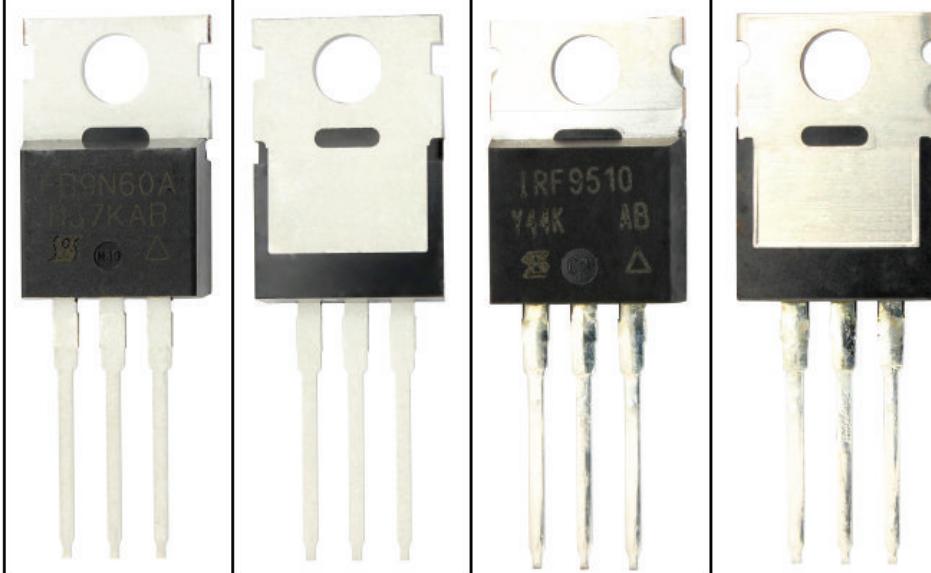
#### Note

- $M^* = 0.052$  inches to  $0.064$  inches (dimension including protrusion), heatsink hole for HVM

Package Picture

ASE

Xi'an



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